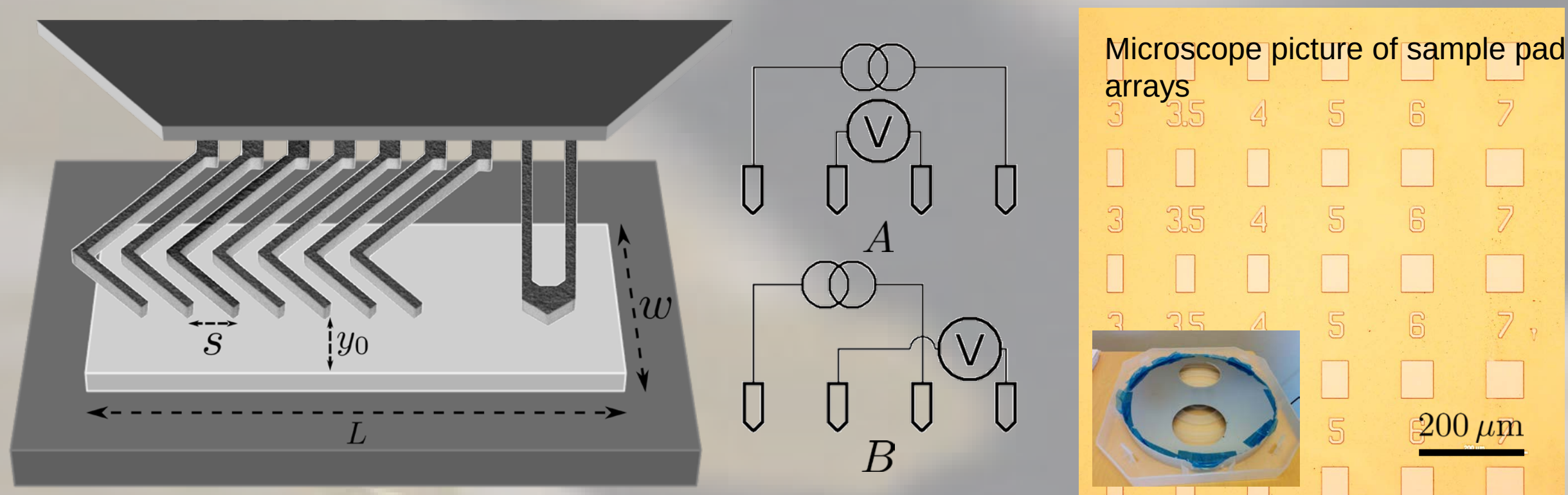


Precision of Micro Hall Effect Measurements in Scribe Line Test Pads of B-doped SiGe

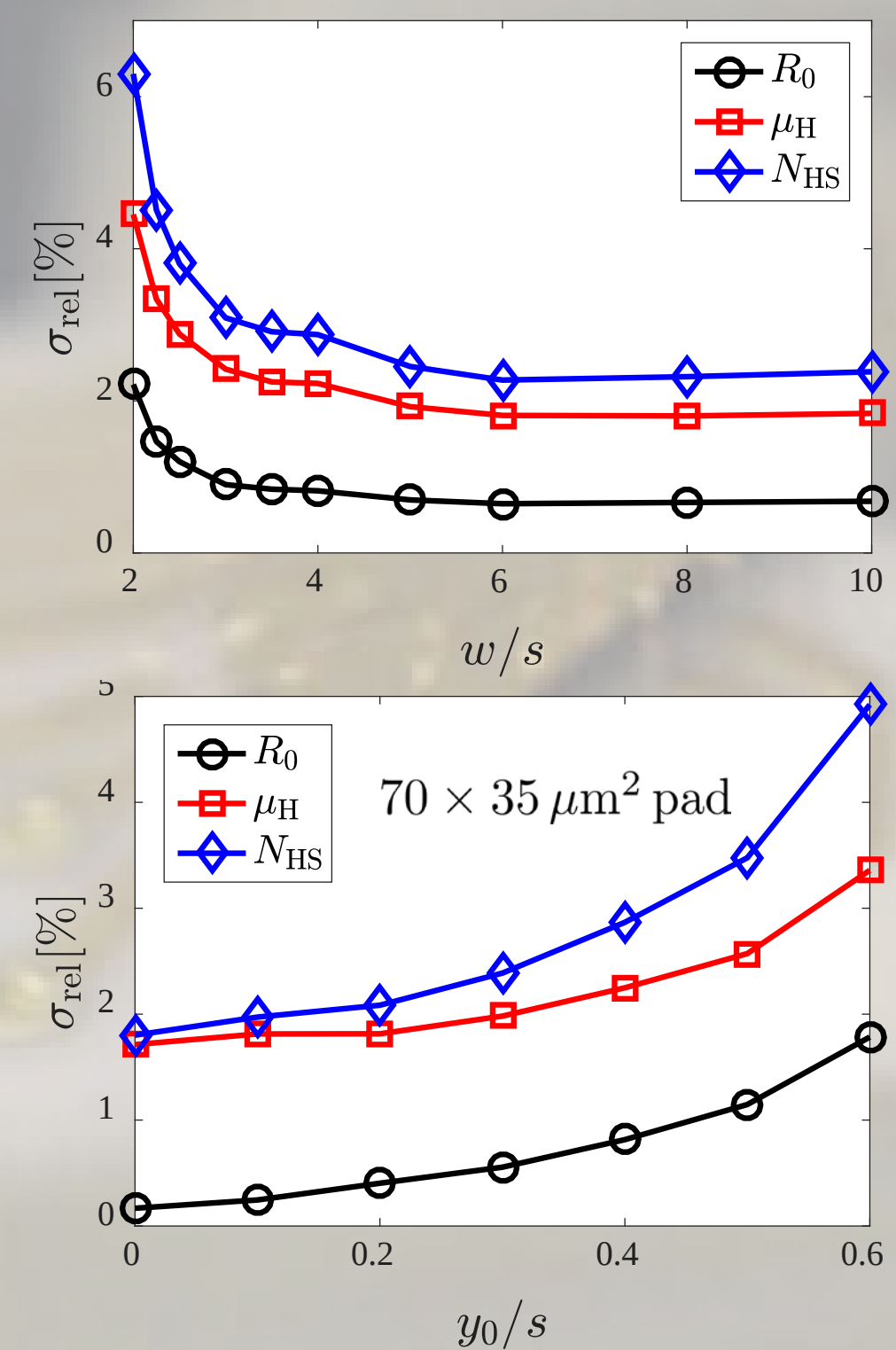
By: Maria-Louise Witthøft^a, Frederik W. Østerberg^a, Janusz Bogdanowicz^b, Andreas Schulze^b, Wilfried Vandervorst^{b,c}, Rong Lin^d, Henrik H. Henrichsen^d, Peter F. Nielsen^d, Ole Hansen^a & Dirch H. Petersen^a

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Measurement Technique

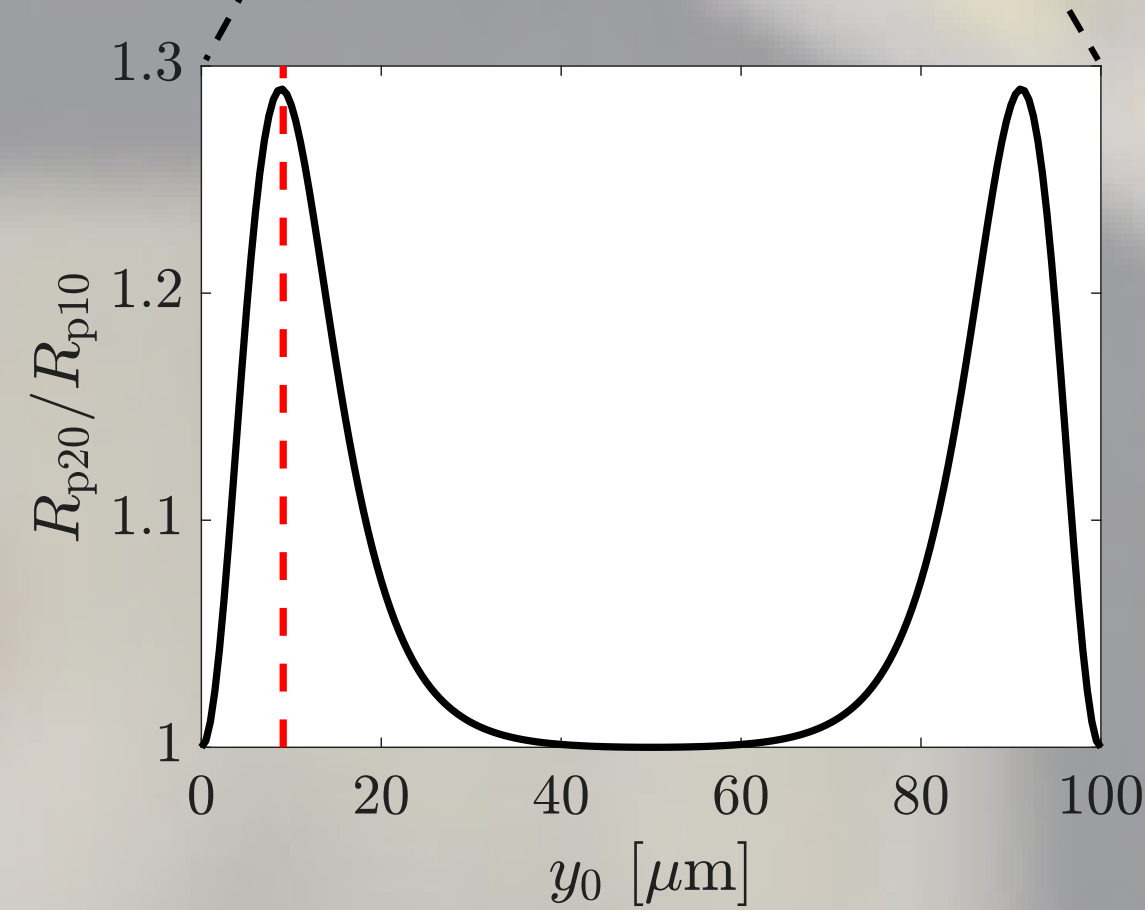
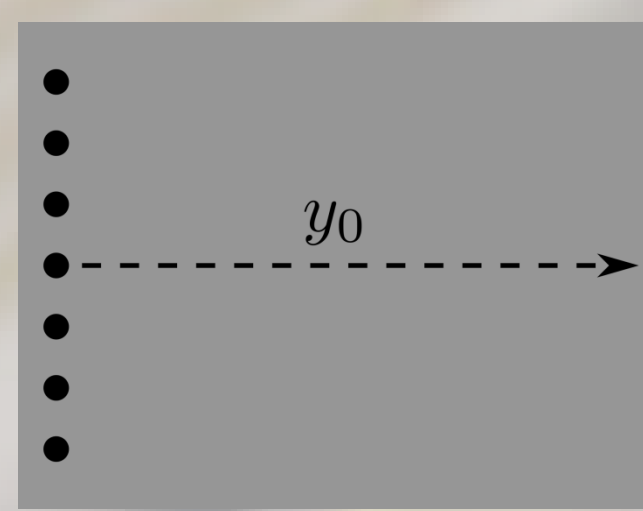


Monte Carlo Simulation of Measurement Errors

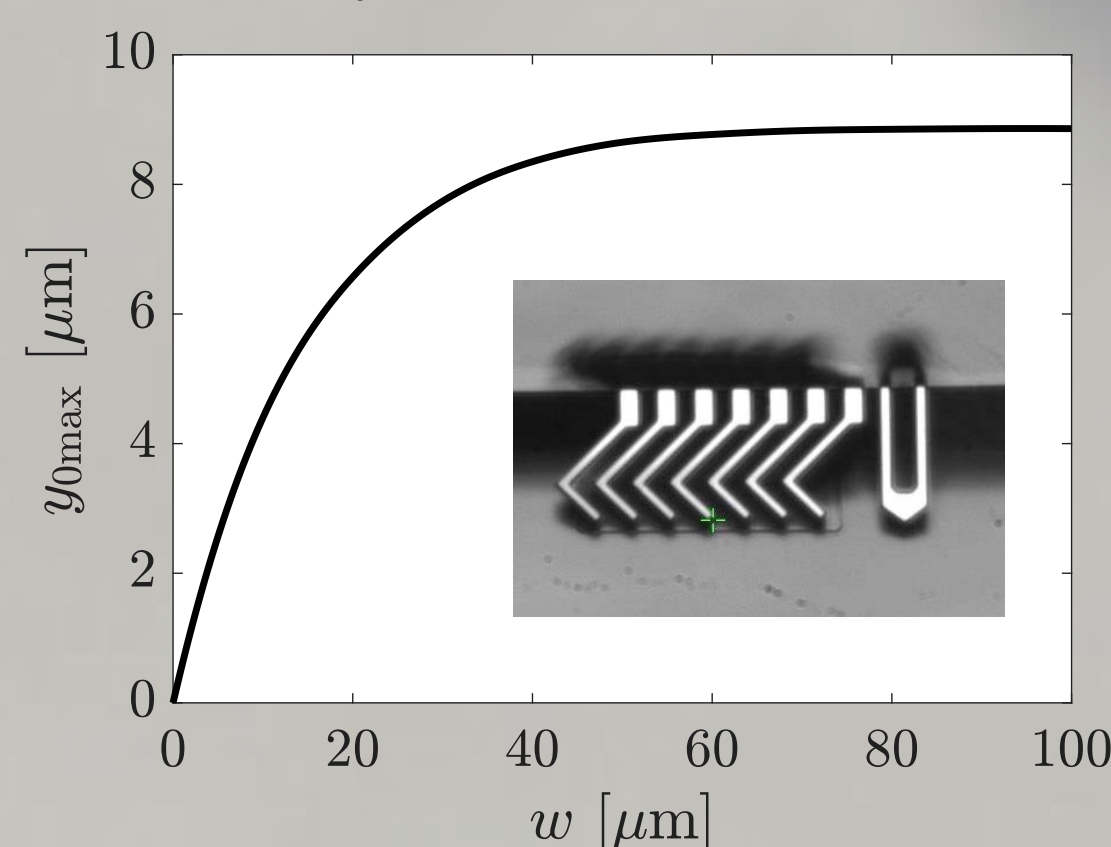


Distance to the Edge

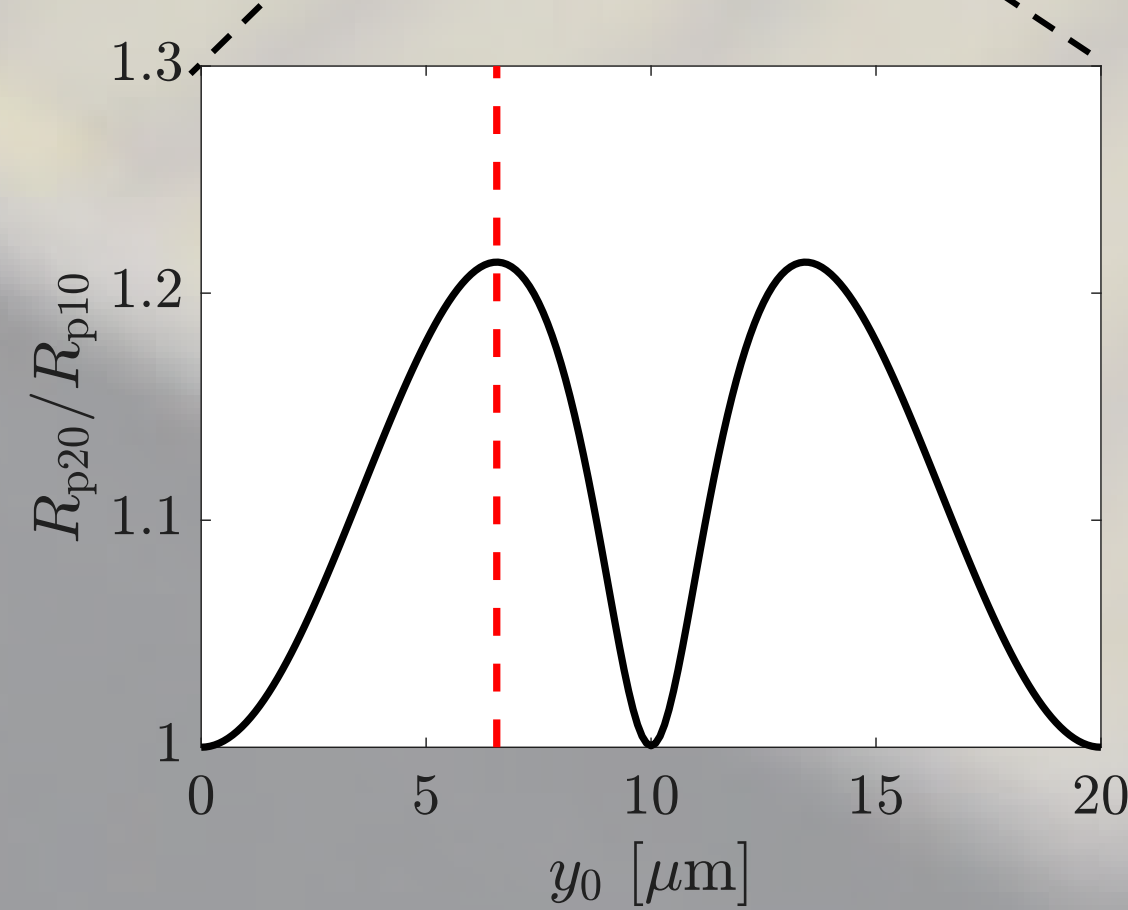
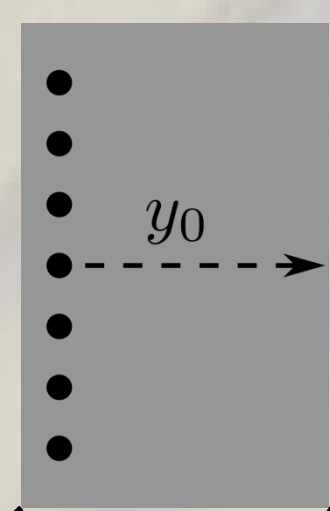
Determining probe distance to the edge, y_0 , on a big pad (100 μm)



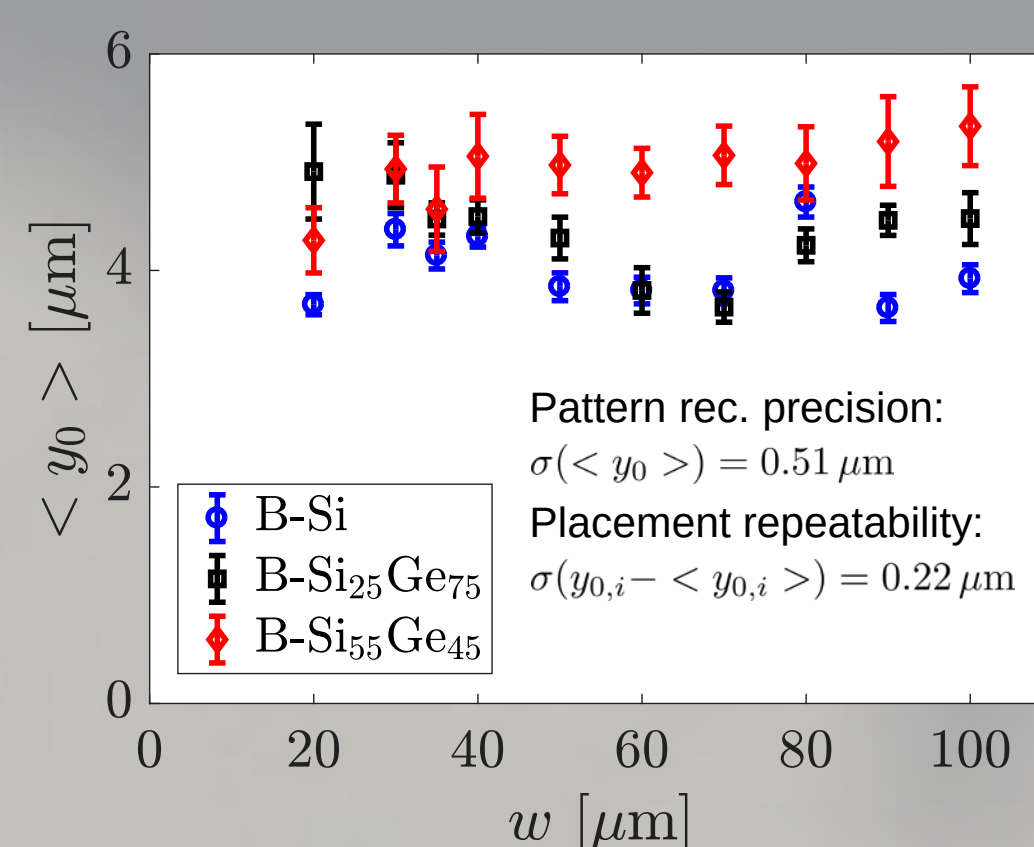
Maximum probe landing distance from the edge, $y_{0\text{max}}$, vs. pad size, w , to ensure correct y_0 calculation



Determining probe distance to the edge, y_0 , on a small pad (20 μm)



Standard deviation on mean distance to the edge, $\langle y_0 \rangle$, vs. pad size, w , for different samples



Experimental Measurement Errors on B-doped SiGe Pads

